

Description

The XPX300P04LL uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

 $V_{DS} = -40V I_{D} = -300A$

 $R_{DS(ON)}$ < 1.6m Ω @ V_{GS} =-10V

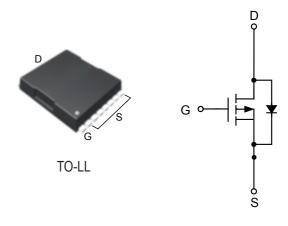
Application

Battery protection

Load switch

Uninterruptible power supply

Pin Description



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)	
XPX300P04LL	TOLLA-8L	XPX300P04LLXXX YYYY	2000	

Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol Parameter		Rating	Units	
V _{DS}	Drain-Source Voltage	-40	V	
Vgs	Gate-Source Voltage	±20	V	
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ -10V ¹	-300	А	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ -10V ¹	-180	А	
Ірм	Pulsed Drain Current ²	-1240	А	
EAS	Single Pulse Avalanche Energy ³	1820	mJ	
las	Avalanche Current	-100	А	
P _D @T _C =25°C	Total Power Dissipation ⁴	350	W	
Тѕтс	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
Reja	Thermal Resistance Junction-Ambient ¹	40	°C/W	
ReJC Thermal Resistance Junction-Case ¹		0.9	°C/W	



Electrical Characteristics (T_J=25℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-40	-44		V
△BVbss/△TJ	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =-1mA		-0.023		V/°C
Rds(on)	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-20A		1.6	2.0	mΩ
		V _{GS} =-4.5V , I _D =-10A		2.1	3.5	
V _{GS(th)}	Gate Threshold Voltage	V_{GS} = V_{DS} , I_{D} =-250uA	-1.2	-1.6	-2.5	V
	Drain-Source Leakage Current	V _{DS} =-40V , V _{GS} =0V , T _J =25°C			1	uA
IDSS		V _{DS} =-40V , V _{GS} =0V , T _J =55°C			5	
Igss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA
gfs	Forward Transconductance	V _{DS} =-15V , I _D =-12A		225		S
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		2.2		Ω
Qg	Total Gate Charge (-4.5V)			436		
Qgs	Gate-Source Charge	V _{DS} =-20V , V _{GS} =-10V , I _D =-40	1	46		nC
Qgd	Gate-Drain Charge	.5 .0	1	64		
Td(on)	Turn-On Delay Time	.,,		62		
Tr	Rise Time	V_{DD} =-20V , V_{GS} =-10V , R_G =3.0 Ω ,		64		ns
Td(off)	Turn-Off Delay Time	I _D =-40	-	236		115
T _f	Fall Time	_		40		
Ciss	Input Capacitance			18256		
Coss	Output Capacitance	V_{DS} =-20V , V_{GS} =0V , f =1MHz		3800		pF
Crss	Reverse Transfer Capacitance			1870		
ls	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current			-280	Α
VsD	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C			-1.2	V

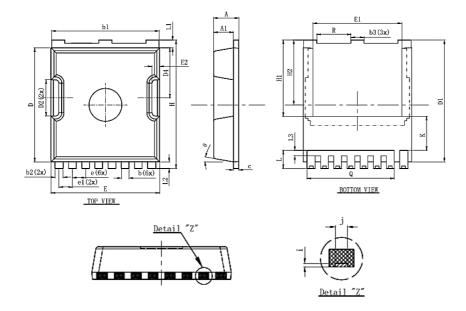
Note:

- 1. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
- 2. The data tested by pulsed , pulse width $\, \leqq \,$ 300us , duty cycle $\, \leqq \,$ 2%
- 3、The EAS data shows Max. rating . The test condition is VDD=-32V,VGS=-10V,L=0.1mH,IAS=-100A
- 4. The power dissipation is limited by 150 $^{\circ}\mathrm{C}$ junction temperature
- 5. The data is theoretically the same as ID and IDM, in real applications, should be limited by total power dissipation.

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Package Mechanical Data-TOLLA-8-XZ Single



Cumbal	Dimensions In Millimeters		
Symbol —	Min.	Nom	Max.
A	2.2	2.3	2.4
A1	1.7	1.8	1.9
b	0.6	0.7	0.8
b1	9.7	9.8	9.9
b2	0.65	0.75	0.85
b3	1.1	1.2	1.3
С	0.4	0.5	0.6
D	10.3	10.4	10.5
D1	11.0	11.1	11.2
D2	3.2	3.3	3.4
D4	4.47	4.57	4.67
Е	9.8	9.9	10.0
E1	8.0	8.1	8.2
E2	0.5	0.6	0.7
е	1.200 (BSC)		
e1	1.225 (BSC)		
Н	11.6 11.7 11.8		11.8
H1	6.95BSC		
H2	5.9BSC		
i	0.1REF		
j	0.350REF		
K	3.100REF		
L	1.55	1.65	1.75
L1	0.6	0.7	0.8
L2	0.5	0.6	0.7
L3	0.4	0.5	0.6
Q	7.95REF		
R	3.0	3.1	3.2
θ	10°REG		



Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245℃±5℃	5sec±1sec
Pb-Free device	260℃+0/-5℃	5sec±1sec



This integrated circuit can be damaged by ESD UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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